

2SB647, 2SB647A

Silicon PNP Epitaxial

REJ03G0648-0200
(Previous ADE-208-1025)
Rev.2.00
Aug.10.2005

Application

- Low frequency power amplifier
- Complementary pair with 2SD667/A

Outline

RENESAS Package code: PRSS0003DC-A
(Package name: TO-92 Mod)



1. Emitter
2. Collector
3. Base

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	2SB647	2SB647A	Unit
Collector to base voltage	V_{CBO}	-120	-120	V
Collector to emitter voltage	V_{CEO}	-80	-100	V
Emitter to base voltage	V_{EBO}	-5	-5	V
Collector current	I_C	-1	-1	A
Collector peak current	$i_{C(peak)}$	-2	-2	A
Collector power dissipation	P_C	0.9	0.9	W
Junction temperature	T_j	150	150	°C
Storage temperature	T_{stg}	-55 to +150	-55 to +150	°C

Electrical Characteristics

(Ta = 25°C)

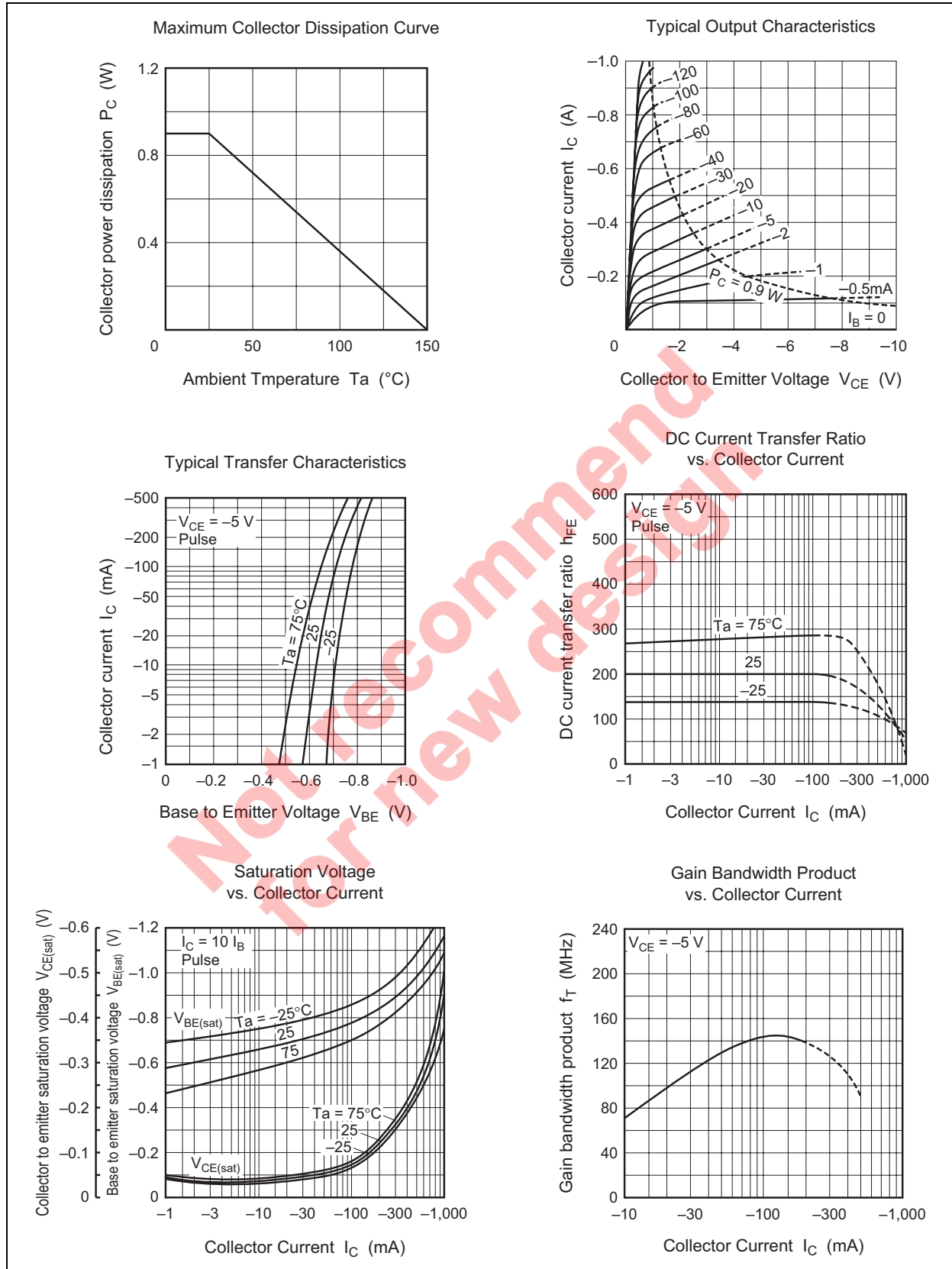
Item	Symbol	2SB647			2SB647A			Unit	Test conditions
		Min	Typ	Max	Min	Typ	Max		
Collector to base breakdown voltage	$V_{(BR)CBO}$	-120	—	—	-120	—	—	V	$I_C = -10 \mu A, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-80	—	—	-100	—	—	V	$I_C = -1 mA, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-5	—	—	-5	—	—	V	$I_E = -10 \mu A, I_C = 0$
Collector cutoff current	I_{CBO}	—	—	-10	—	—	-10	μA	$V_{CB} = -100 V, I_E = 0$
DC current transfer ratio	h_{FE1}^{*1}	60	—	320	60	—	200		$V_{CE} = -5 V, I_C = -150 mA^{*2}$
	h_{FE2}	30	—	—	30	—	—		$V_{CE} = -5 V, I_C = -500 mA^{*2}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	-1	—	—	-1	V	$I_C = -500 mA, I_B = -50 mA^{*2}$
Base to emitter voltage	V_{BE}	—	—	-1.5	—	—	-1.5	V	$V_{CE} = -5 V, I_C = -150 mA^{*2}$
Gain bandwidth product	f_T	—	140	—	—	140	—	MHz	$V_{CE} = -5 V, I_C = -150 mA$
Collector output capacitance	C_{ob}	—	20	—	—	20	—	pF	$V_{CB} = -10 V, I_E = 0, f = 1 MHz$

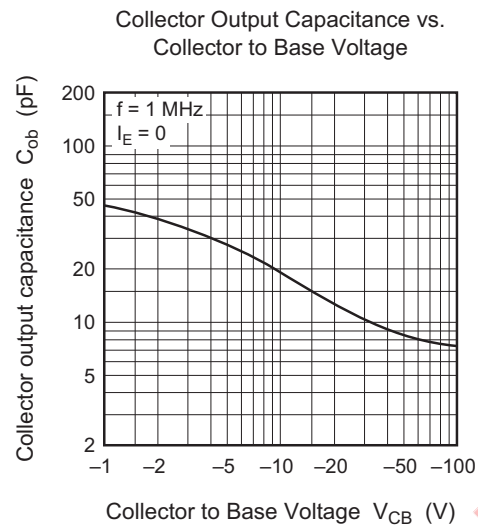
Notes: 1. The 2SB647 and 2SB647A are grouped by h_{FE1} as follows.

2. Pulse test

	B	C	D
2SB647	—	100 to 200	160 to 320
2SB647A	60 to 120	100 to 200	—

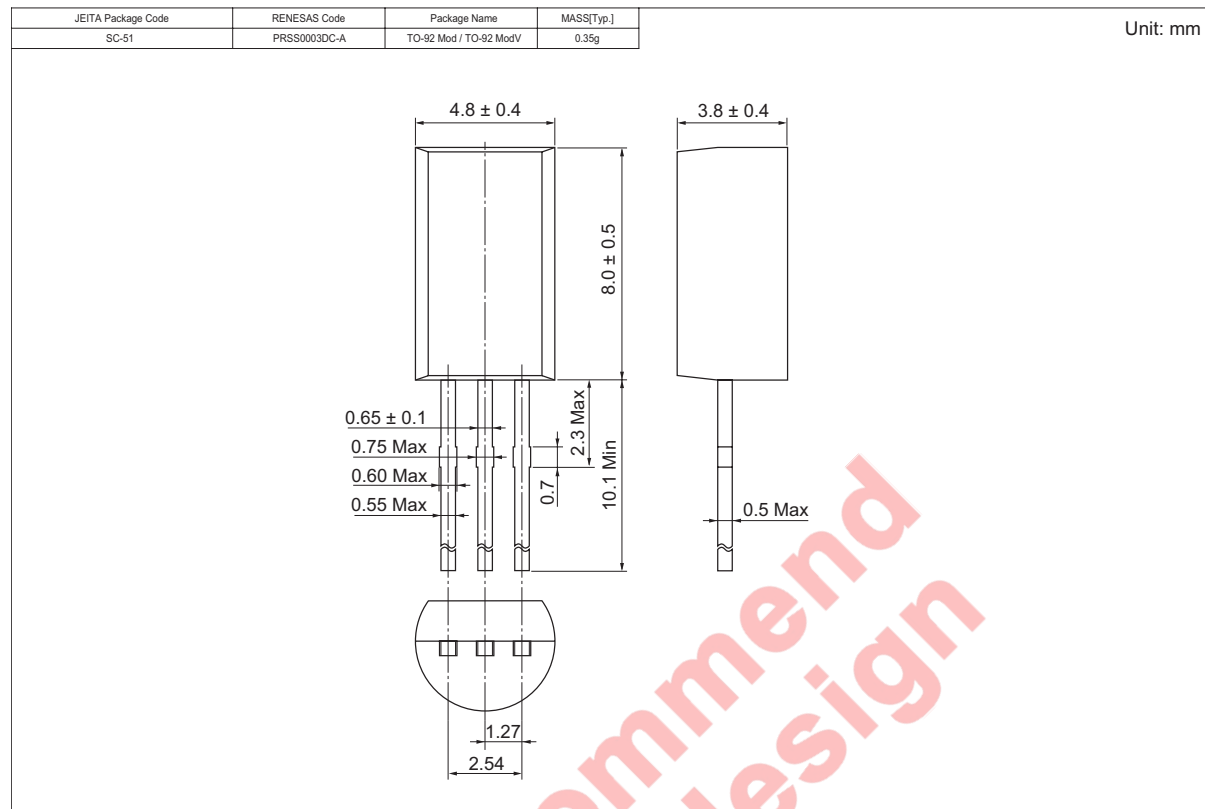
Main Characteristics





Not recommended
for new design

Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SB647CTZ-E	2500	Hold Box, Radial Taping
2SB647DTZ-E		
2SB647ABTZ-E		
2SB647ACTZ-E		

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A
Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited

Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology Hong Kong Ltd.

7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong
Tel: <852> 2265-6688, Fax: <852> 2730-6071

Renesas Technology Taiwan Co., Ltd.

10th Floor, No.99, Fushing North Road, Taipei, Taiwan
Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology (Shanghai) Co., Ltd.

Unit2607 Ruijing Building, No.205 Maoming Road (S), Shanghai 200020, China
Tel: <86> (21) 6472-1001, Fax: <86> (21) 6415-2952

Renesas Technology Singapore Pte. Ltd.

1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632
Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd.

Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea
Tel: <82> 2-796-3115, Fax: <82> 2-796-2145

Renesas Technology Malaysia Sdn. Bhd.

Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: <603> 7955-9390, Fax: <603> 7955-9510